



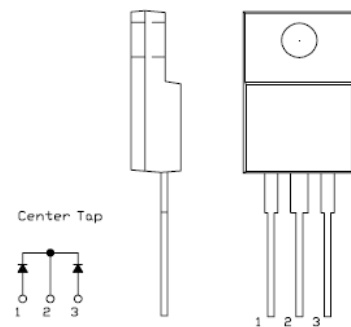
MURF1660CT ULTRAFAST PLASTIC RECTIFIER

Applications:

- Switching Power Supply
- Power Switching Circuits
- General Purpose

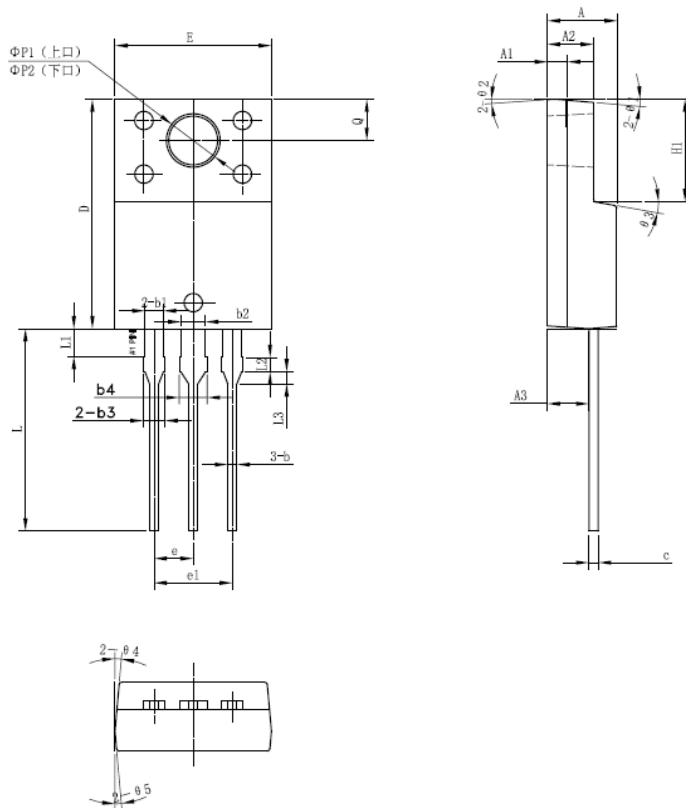
Features:

- Ultra-Fast Switching
- High Current Capability
- Low Reverse Leakage Current
- High Surge Current Capability
- Plastic Material has UL Flammability Classification 94V-0
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



OUTLINE DRAWING

Mechanical Dimensions: In mm



SYMBOL	MIN.	TYP.	MAX.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85
c	0.55	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e		2.55	
e1		5.10	
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
ΦP1(上□)	3.30	3.50	3.70
ΦP2(下□)	2.99	3.19	3.39
Q	2.50	2.70	2.90
θ1		5°	
θ2		4°	
θ3		10°	
θ4		5°	
θ5		5°	

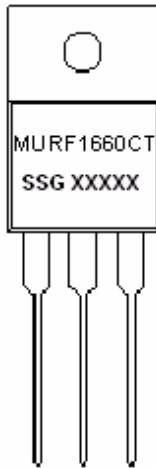
ITO-220AB



Technical Data
Data Sheet N0354, Rev. -

Green Products

Marking Diagram:



Where XXXXX is YYWWL

MUR = Device Type
 F = Package type
 16 = Forward Current (16A)
 60 = Reverse Voltage (600V)
 CT = Configuration
 SSG = SSG
 YY = Year
 WW = Week
 L = Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MURF1660CT	ITO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	600	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle @Tc=90°C, rectangular wave form	16	A
Max. Peak One Cycle Non-Repetitive Surge Current (Per leg)	I_{FSM}	8.3ms, Half Sine pulse	110	A



Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop* (per leg)	V_{F1}	@ 8A, Pulse, $T_J = 25^\circ\text{C}$	2.2	V
Max. Reverse Current*	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25^\circ\text{C}$	5	μA
	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 150^\circ\text{C}$	500	μA
Max. Reverse Recovery Time	t_{rr}	$I_F=500\text{mA}$, $I_R=1\text{A}$, and $I_{rm}=250\text{mA}$	50	ns
RSM Isolation Voltage ($t=1.0$ second, R.H.< =30%, $T_A=25^\circ\text{C}$)	V_{iso}	Clip mouting, the epoxy body away from the heatsink edge by more than 0.110" along the lead direction.	4500	V
		Clip mouting, the epoxy body is inside the heatsink	3500	
		Screw mounting, the epoxy body is inside the heatsink	1500	

* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +150	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	5.0	$^\circ\text{C/W}$
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

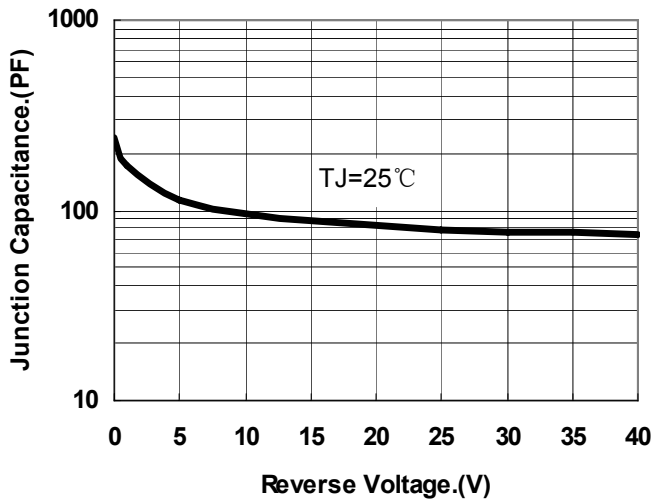


Fig.1-Typical Junction Capacitance

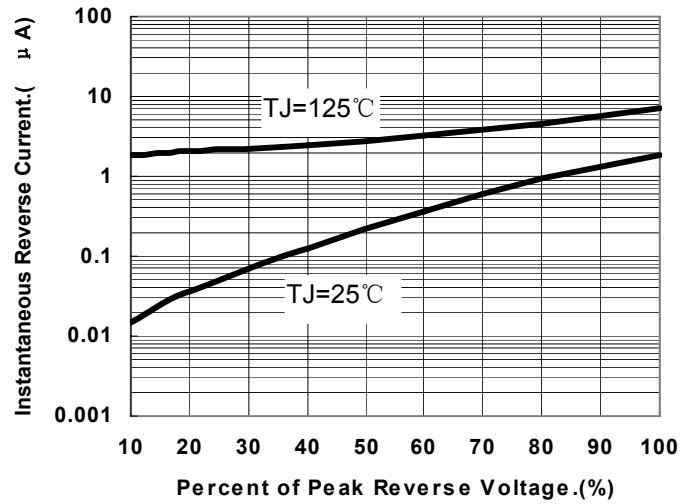


Fig.2-Typical Reverse Characteristics

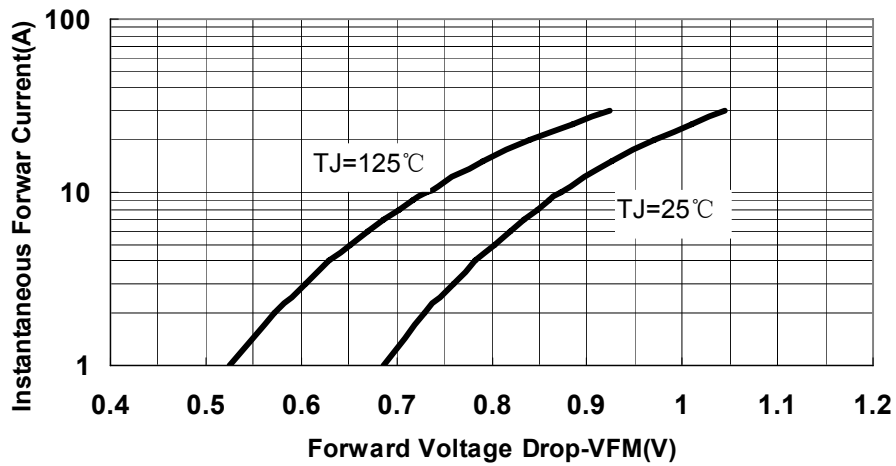


Fig.3-Typical Instantaneous Forward Voltage Characteristics



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